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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.5GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8548evjavhd

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2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	BV _{DD} = 3.3 V BV _{DD} = 2.5 V	1
	45(default) 45(default)	BV _{DD} = 3.3 V BV _{DD} = 2.5 V	
PCI signals	25	OV _{DD} = 3.3 V	2
	45(default)		
DDR signal	18 36 (half strength mode)	GV _{DD} = 2.5 V	3
DDR2 signal	18 36 (half strength mode)	GV _{DD} = 1.8 V	3
TSEC/10/100 signals	45	L/TV _{DD} = 2.5/3.3 V	
DUART, system control, JTAG	45	OV _{DD} = 3.3 V	—
12C	150	OV _{DD} = 3.3 V	_

Table 3. Output Drive Capability

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.

2. The drive strength of the PCI interface is determined by the setting of the PCI_GNT1 signal at reset.

3. The drive strength of the DDR interface in half-strength mode is at $T_i = 105^{\circ}C$ and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

- 1. V_{DD}, AV_{DD}, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD}, TV_{DD}, XV_{DD}
- 2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

4 Input Clocks

This section discusses the timing for the input clocks.

4.1 System Clock Timing

The following table provides the system clock (SYSCLK) AC timing specifications for the device.

Table 5. SYSCLK AC Timing Specifications

At recommended operating conditions (see Table 2) with $OV_{DD} = 3.3 \text{ V} \pm 165 \text{ mV}$.

Parameter/Condition	Symbol	Min	Тур	Мах	Unit	Notes
SYSCLK frequency	f _{SYSCLK}	16	—	133	MHz	1, 6, 7, 8
SYSCLK cycle time	t _{SYSCLK}	7.5	—	60	ns	6, 7, 8
SYSCLK rise and fall time	t _{KH} , t _{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t _{KHK} /t _{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	±150	ps	4, 5

Notes:

- Caution: The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, "CCB/SYSCLK PLL Ratio," and Section 20.3, "e500 Core PLL Ratio," for ratio settings.
- 2. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
- 3. Timing is guaranteed by design and characterization.
- 4. This represents the total input jitter—short term and long term—and is guaranteed by design.
- 5. The SYSCLK driver's closed loop jitter bandwidth must be <500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter.
- 6. This parameter has been adjusted slower according to the workaround for device erratum GEN 13.
- 7. For spread spectrum clocking. Guidelines are + 0% to -1% down spread at modulation rate between 20 and 60 kHz on SYSCLK.
- 8. System with operating core frequency less than 1200 MHz must limit SYSCLK frequency to 100 MHz maximum.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal must be greater than 2x the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that $GV_{DD}(typ) = 2.5 \text{ V}$ for DDR SDRAM, and $GV_{DD}(typ) = 1.8 \text{ V}$ for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when $GV_{DD}(typ) = 1.8 \text{ V}.$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV _{DD}	1.71	1.89	V	1
I/O reference voltage	MV _{REF}	$0.49 \times GV_{DD}$	$0.51 imes GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} – 0.04	MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	MV _{REF} + 0.125	GV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	-0.3	MV _{REF} – 0.125	V	—
Output leakage current	I _{OZ}	-50	50	μA	4
Output high current (V _{OUT} = 1.420 V)	I _{ОН}	-13.4	—	mA	—
Output low current (V _{OUT} = 0.280 V)	I _{OL}	13.4	—	mA	—

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.

2. MV_{REF} is expected to be equal to 0.5 × GV_{DD} , and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

This table provides the DDR2 I/O capacitance when $GV_{DD}(typ) = 1.8$ V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Input/output capacitance: DQ, DQS, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, DQS	C _{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

DUART

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the device.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface.

Table 20. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = V_{DD})$	I _{IN}	-	±5	μA
High-level output voltage ($OV_{DD} = min, I_{OH} = -2 mA$)	V _{OH}	2.4	_	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V _{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface.

Table 21. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	f _{CCB} /1,048,576	baud	1, 2
Maximum baud rate	f _{CCB} /16	baud	1, 2, 3
Oversample rate	16		1, 4

Notes:

1. Guaranteed by design.

2. f_{CCB} refers to the internal platform clock.

3. Actual attainable baud rate is limited by the latency of interrupt processing.

4. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

12.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the JTAG interface.

Parameter	Symbol ¹	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current ($V_{IN}^{1} = 0 V \text{ or } V_{IN} = V_{DD}$)	I _{IN}	—	±5	μΑ
High-level output voltage ($OV_{DD} = min, I_{OH} = -2 mA$)	V _{OH}	2.4	—	V
Low-level output voltage (OV _{DD} = min, I _{OL} = 2 mA)	V _{OL}	—	0.4	V

 Table 43. JTAG DC Electrical Characteristics

Note:

1. Note that the symbol V_{IN} in this case, represents the OV_{IN}

12.2 JTAG AC Electrical Specifications

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 32.

Parameter	Symbol ²	Min	Мах	Unit	Notes
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} & t _{JTGF}	0	2	ns	6
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 0	_	ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	20 25		ns	4

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)¹

JTAG

Figure 31 provides the $\overline{\text{TRST}}$ timing diagram.







Figure 32. Boundary-Scan Timing Diagram

Parameter	Symbol	Min	Мах	Unit
Supply voltage 2.5 V	BV _{DD}	2.37	2.63	V
High-level input voltage	V _{IH}	1.70	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.7	V
Input current ($BV_{IN}^{1} = 0 V \text{ or } BV_{IN} = BV_{DD}$)	Ι _{ΙΗ}	_	10	μΑ

Table 50. GP_{IN} DC Electrical Characteristics (2.5 V DC)

Note:

1. The symbol $\mathsf{BV}_{\mathsf{IN}}$ in this case, represents the $\mathsf{BV}_{\mathsf{IN}}$ symbol referenced in Table 1.

15 PCI/PCI-X

This section describes the DC and AC electrical specifications for the PCI/PCI-X bus of the device.

Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

15.1 PCI/PCI-X DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI/PCI-X interface.

Table 51. PCI/PCI-X DC Electrical Characteristics¹

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V	—
Low-level input voltage	V _{IL}	-0.3	0.8	V	—
Input current ($V_{IN} = 0 V \text{ or } V_{IN} = V_{DD}$)	I _{IN}	—	±5	μA	2
High-level output voltage ($OV_{DD} = min, I_{OH} = -2 mA$)	V _{OH}	2.4	—	V	—
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V _{OL}	—	0.4	V	—

Notes:

1. Ranges listed do not meet the full range of the DC specifications of the PCI 2.2 Local Bus Specifications.

2. The symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

15.2 PCI/PCI-X AC Electrical Specifications

This section describes the general AC timing parameters of the PCI/PCI-X bus. Note that the clock reference CLK is represented by SYSCLK when the PCI controller is configured for synchronous mode and by PCIn_CLK when it is configured for asynchronous mode.

to AC-coupling. Its value could be ranged from 140 to 240 Ω depending on the clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50- Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the SerDes reference clock's differential input amplitude requirement (between 200 and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω . Consult a clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.



Figure 45. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

Figure 46 shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with the SerDes reference clock input's DC requirement.



Figure 46. Single-Ended Connection (Reference Only)

PCI Express



Figure 48. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

Table 57 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps \pm 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
V _{RX-DIFFp-p}	Differential peak-to-peak input voltage	0.175	_	1.200	V	$V_{RX-DIFFp-p} = 2 \times V_{RX-D+} - V_{RX-D-} $. See Note 2.
T _{RX-EYE}	Minimum receiver eye width	0.4	_	_	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.
T _{RX-EYE-MEDIAN-to-} MAX-JITTER	Maximum time between the jitter median and maximum deviation from the median	_	_	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.

Table 57. Differential Receiver (RX) Input Specifications

PCI Express

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50. to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50- Ω probes—see Figure 50). Note that the series capacitors, CTX, are optional for the return loss measurement.



Figure 49. Minimum Receiver Eye Timing and Voltage Compliance Specification

17.5.1 Compliance Test and Measurement Load

The AC timing and voltage parameters must be verified at the measurement point, as specified within 0.2 inches of the package pins, into a test/measurement load shown in Figure 50.

NOTE

The allowance of the measurement point to be within 0.2 inches of the package pins is meant to acknowledge that package/board routing may benefit from D+ and D- not being exactly matched in length at the package pin boundary.



Figure 50. Compliance Test/Measurement Load

Serial RapidIO

Table 60. Short Run Transmitter	AC Timing Specifications-	–2.5 GBaud
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Characteristic	Symbol	Range		Unit	Notos
Characteristic	Symbol	Min	Max	Unit	Notes
Output voltage	V _O	-0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V _{DIFFPP}	500	1000	mV p-p	_
Deterministic jitter	J _D	—	0.17	UI p-p	_
Total jitter	J _T	—	0.35	UI p-p	_
Multiple output skew	S _{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	400	400	ps	±100 ppm

Table 61. Short Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Characteristic Symbol Range		Unit	Notos	
Characteristic	Cymbol	Min	Max	Onic	NOIES
Output voltage	V _O	-0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V _{DIFFPP}	500	1000	mVp-p	_
Deterministic jitter	J _D	_	0.17	UI p-p	_
Total jitter	J _T	_	0.35	UI p-p	_
Multiple output skew	S _{MO}		1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	320	320	ps	±100 ppm

Table 62. Long Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Characteristic Symbol Range		Notos		
	Symbol	Min	Max	Onic	Notes
Output voltage	V _O	-0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V _{DIFFPP}	800	1600	mVp-p	_
Deterministic jitter	J _D	—	0.17	UI p-p	_
Total jitter	J _T	—	0.35	UI p-p	_
Multiple output skew	S _{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	800	800	ps	±100 ppm

Package Description

Signal	Package Pin Number	Pin Type	Power Supply	Notes		
Reserved	U20, V22, W20, Y22	_	—	15		
Reserved	U21, V23, W21, Y23	—	—	15		
SD_PLL_TPD	U28	0	XV _{DD}	24		
SD_REF_CLK	T28	I	XV _{DD}	—		
SD_REF_CLK	T27	I	XV _{DD}	—		
Reserved	AC1, AC3	—	—	2		
Reserved	M26, V28	—	—	32		
Reserved	M25, V27	—	—	34		
Reserved	M20, M21, T22, T23	—	—	38		
	General-Purpose Output					
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	0	BV _{DD}	_		
	System Control					
HRESET	AG17	I	OV _{DD}	_		
HRESET_REQ	AG16	0	OV _{DD}	29		
SRESET	AG20	I	OV _{DD}	_		
CKSTP_IN	AA9	I	OV _{DD}	_		
CKSTP_OUT	AA8	0	OV _{DD}	2, 4		
Debug						
TRIG_IN	AB2	I	OV _{DD}	—		
TRIG_OUT/READY/QUIESCE	AB1	0	OV _{DD}	6, 9, 19, 29		
MSRCID[0:1]	AE4, AG2	0	OV _{DD}	5, 6, 9		
MSRCID[2:4]	AF3, AF1, AF2	0	OV _{DD}	6, 19, 29		
MDVAL	AE5	0	OV _{DD}	6		
CLK_OUT	AE21	0	OV _{DD}	11		
	Clock					
RTC	AF16	I	OV _{DD}	—		
SYSCLK	AH17	I	OV _{DD}	—		
JTAG						
ТСК	AG28	Ι	OV _{DD}	—		
TDI	AH28	Ι	OV _{DD}	12		
TDO	AF28	0	OV _{DD}	_		
TMS	AH27	I	OV _{DD}	12		
TRST	AH23	I	OV _{DD}	12		

Package Description

Signal	Package Pin Number	Pin Type	Power Supply	Notes			
BV _{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV _{DD}	_			
V _{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V _{DD}	—			
SV _{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV _{DD}	_			
XV _{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV _{DD}	_			
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	_	26			
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	_	26			
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	_	26			
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	_	26			
AVDD_PLAT	AH19	Powerfor CCB PLL (1.1 V)	—	26			
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)		26			
SENSEVDD	M14	0	V_{DD}	13			
SENSEVSS	M16	_		13			
Analog Signals							
MVREF	A18	I Reference voltage signal for DDR	MVREF				
SD_IMP_CAL_RX	L28	I	200 Ω to GND	_			
SD_IMP_CAL_TX	AB26	I	100 Ω to GND				

Table 72. MPC8547E Pinout Listing (continued)

Package Description

Signal	Package Pin Number	Pin Type	Power Supply	Notes
UDE	AH16	I	OV _{DD}	—
MCP	AG19	I	OV _{DD}	—
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV _{DD}	_
IRQ[8]	AF19	I	OV _{DD}	—
IRQ[9]/DMA_DREQ3	AF21	I	OV _{DD}	1
IRQ[10]/DMA_DACK3	AE19	I/O	OV _{DD}	1
IRQ[11]/DMA_DDONE3	AD20	I/O	OV _{DD}	1
IRQ_OUT	AD18	0	OV _{DD}	2, 4
	Ethernet Management Interface			
EC_MDC	AB9	0	OV _{DD}	5, 9
EC_MDIO	AC8	I/O	OV _{DD}	—
	Gigabit Reference Clock		•	•
EC_GTX_CLK125	V11	I	LV _{DD}	—
Tł	ree-Speed Ethernet Controller (Gigabit Ethern	et 1)	•	
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV _{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	0	LV _{DD}	5, 9
TSEC1_COL	R4	I	LV _{DD}	—
TSEC1_CRS	V5	I/O	LV _{DD}	20
TSEC1_GTX_CLK	U7	0	LV _{DD}	—
TSEC1_RX_CLK	U3	I	LV _{DD}	—
TSEC1_RX_DV	V2	I	LV _{DD}	—
TSEC1_RX_ER	T1	I	LV _{DD}	—
TSEC1_TX_CLK	Т6	I	LV _{DD}	—
TSEC1_TX_EN	U9	0	LV _{DD}	30
TSEC1_TX_ER	Τ7	0	LV _{DD}	—
GPIN[0:7]	P2, R2, N1, N2, P3, M2, M1, N3	I	LV _{DD}	103
GPOUT[0:5]	N9, N10, P8, N7, R9, N5	0	LV _{DD}	—
cfg_dram_type0/GPOUT6	R8	0	LV _{DD}	5, 9
GPOUT7	N6	0	LV _{DD}	-
Reserved	P1	_	—	104
Reserved	R6	_	—	104
Reserved	P6	_	-	15
Reserved	N4			105

Signal	Package Pin Number	Pin Type	Power Supply	Notes				
JTAG								
ТСК	AG28	I	OV _{DD}	_				
TDI	AH28	I	OV _{DD}	12				
TDO	AF28	0	OV _{DD}	—				
TMS	AH27	I	OV _{DD}	12				
TRST	AH23	I	OV _{DD}	12				
	DFT	I						
L1_TSTCLK	AC25	I	OV _{DD}	25				
L2_TSTCLK	AE22	I	OV _{DD}	25				
LSSD_MODE	AH20	I	OV _{DD}	25				
TEST_SEL	AH14	I	OV _{DD}	109				
	Thermal Management	•						
THERM0	AG1		—	14				
THERM1	AH1		—	14				
	Power Management							
ASLEEP	AH18	0	OV _{DD}	9, 19, 29				
	Power and Ground Signals							
GND	 A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27 	_						
OV _{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV _{DD}	—				
LV _{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV _{DD}	_				

20.3 e500 Core PLL Ratio

This table describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LBCTL, LALE, and LGPL2 at power up, as shown in this table.

Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio	Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio
000	4:1	100	2:1
001	9:2	101	5:2
010	Reserved	110	3:1
011	3:2	111	7:2

Table 82. e500 Core to	CCB Clock Ratio
------------------------	------------------------

20.4 Frequency Options

Table 83This table shows the expected frequency values for the platform frequency when using a CCB clock to SYSCLK ratio in comparison to the memory bus clock speed.

CCB to SYSCLK Ratio	SYSCLK (MHz)								
	16.66	25	33.33	41.66	66.66	83	100	111	133.33
			ļ	Platform/C	CB Freque	ency (MHz)		
2									
3								333	400
4						333	400	445	533
5					333	415	500		
6					400	500		-	
8				333	533				
9				375					
10			333	417					
12			400	500					
16		400	533		-				
20	333	500		-					

Table 83. Frequency Options of SYSCLK with Respect to Memory Bus Speeds

Note: Due to errata Gen 13 the max sys clk frequency must not exceed 100 MHz if the core clk frequency is below 1200 MHz.

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	R_{\thetaJB}	3	°C/W	3
Die junction-to-case	N/A	$R_{ extsf{ heta}JC}$	0.8	°C/W	4

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Notes:

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
- 3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package	Thermal	Characteristics	for FC-PBGA
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Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	9	°C/W	1, 2

System Design Information

22.10 Guidelines for High-Speed Interface Termination

This section provides the guidelines for high-speed interface termination when the SerDes interface is entirely unused and when it is partly unused.

22.10.1 SerDes Interface Entirely Unused

If the high-speed SerDes interface is not used at all, the unused pin must be terminated as described in this section.

The following pins must be left unconnected (float):

- SD_TX[7:0]
- $\overline{\text{SD}}_{\text{TX}}[7:0]$
- Reserved pins T22, T23, M20, M21

The following pins must be connected to GND:

- SD_RX[7:0]
- <u>SD_RX</u>[7:0]
- SD_REF_CLK
- SD_REF_CLK

NOTE

It is recommended to power down the unused lane through SRDSCR1[0:7] register (offset = $0xE_0F08$) (This prevents the oscillations and holds the receiver output in a fixed state.) that maps to SERDES lane 0 to lane 7 accordingly.

Pins V28 and M26 must be tied to XV_{DD} . Pins V27 and M25 must be tied to GND through a 300- Ω resistor.

In Rev 2.0 silicon, POR configuration pin cfg_srds_en on TSEC4_TXD[2]/TSEC3_TXD[6] can be used to power down SerDes block.

22.10.2 SerDes Interface Partly Unused

If only part of the high-speed SerDes interface pins are used, the remaining high-speed serial I/O pins must be terminated as described in this section.

The following pins must be left unconnected (float) if not used:

- SD_TX[7:0]
- <u>SD_TX</u>[7:0]
- Reserved pins: T22, T23, M20, M21

The following pins must be connected to GND if not used:

- SD_RX[7:0]
- $\overline{\text{SD}_{RX}}[7:0]$
- SD_REF_CLK

Rev. Number	Date	Substantive Change(s)
4	04/2009	 In Table 1, "Absolute Maximum Ratings ¹," and in Table 2, "Recommended Operating Conditions," moved text, "MII management voltage" from LV_{DD}/TV_{DD} to OV_{DD}, added "Ethernet management" to OVDD row of input voltage section. In Table 5, "SYSCLK AC Timing Specifications," added notes 7 and 8 to SYSCLK frequency and cycle
		 time. In Table 36, "MII Management DC Electrical Characteristics," changed all instances of LV_{DD}/OV_{DD} to OV_{DD}. Modified Section 16, "High-Speed Serial Interfaces (HSSI)," to reflect that there is only one SerDes. Modified DDR clk rate min from 133 to 166 MHz. Modified note in Table 75, "Processor Core Clocking Specifications (MPC8548E and MPC8547E), "." In Table 56, "Differential Transmitter (TX) Output Specifications," modified equations in Comments column, and changed all instances of "LO" to "LO." Also added note 8. In Table 57, "Differential Receiver (RX) Input Specifications," modified equations in Comments column, and in note 3, changed "TRX-EYE-MEDIAN-to-MAX-JITTER," to "T_{RX-EYE-MEDIAN-to-MAX-JITTER}." Modified Table 83, "Frequency Options of SYSCLK with Respect to Memory Bus Speeds." Added a note on Section 4.1, "System Clock Timing," to limit the SYSCLK to 100 MHz if the core
		 frequency is less than 1200 MHz In Table 71, "MPC8548E Pinout ListingTable 72, "MPC8547E Pinout ListingTable 73, "MPC8545E Pinout ListingTable 74, "MPC8543E Pinout Listing," added note 5 to LA[28:31]. Added note to Table 83, "Frequency Options of SYSCLK with Respect to Memory Bus Speeds."
3	01/2009	 [Section 4.6, "Platform Frequency Requirements for PCI-Express and Serial RapidIO." Changed minimum frequency equation to be 527 MHz for PCI x8. In Table 5, added note 7. Section 4.5, "Platform to FIFO Restrictions." Changed platform clock frequency to 4.2. Section 8.1, "Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics." Added MII after GMII and add 'or 2.5 V' after 3.3 V. In Table 23, modified table title to include GMII, MII, RMII, and TBI. In Table 24 and Table 25, changed clock period minimum to 5.3. In Table 25, added a note
		 In Table 25, added a hole. In Table 26, Table 27, Table 28, Table 29, and Table 30, removed subtitle from table title. In Table 30 and Figure 15, changed all instances of PMA to TSEC<i>n</i>. In Section 8.2.5, "TBI Single-Clock Mode AC Specifications." Replaced first paragraph. In Table 34, Table 35, Figure 18, and Figure 20, changed all instances of REF_CLK to TSEC<i>n</i>_TX_CLK. In Table 36, changed all instances of OVer to LVer/TVer
		 In Table 37, "MII Management AC Timing Specifications," changed MDC minimum clock pulse width high from 32 to 48 ns. Added new section, Section 16, "High-Speed Serial Interfaces (HSSI)." Section 16.1, "DC Requirements for PCI Express SD_REF_CLK and SD_REF_CLK." Added new paragraph. Section 17.1, "DC Requirements for Serial RapidIO SD_REF_CLK and SD_REF_CLK." Added new paragraph. Added information to Figure 63, both in figure and in note. Section 22.3, "Decoupling Recommendations." Modified the recommendation
		Table 87, "Part Numbering Nomenclature." In Silicon Version column added Ver. 2.1.2.

Table 88. Document Revision History (continued)

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